



Large Area InGaAs p-i-n Photodiode

35PD1M-TO

The 35PD1M-TO, an InGaAs photodiode with a 1mm-diameter photosensitive region and packaged in a TO-46 header, is designed for applications in high sensitivity instrumentation and sensing. Devices are hermetically sealed in a TO-46 header. Low dark current and high dynamic impedance are featured. High reliability is achieved through planar semiconductor design and dielectric-passivation. Chips can also be attached and wire bonded to customer-supplied or other specified packages.

Features

Planar Structure

Dielectric Passivation

High Dynamic Impedance

High Responsivity

Device Characteristics:						
Parameters	Test Conditions		Min	Typ	Max	Units
Dark Current	Class A	-1.0V	-	2	-	nA
	Class B			100		nA
	Class C			1		µA
Capacitance	0V		-	150	-	pF
Responsivity	1300nm		0.9	-	-	A/W
	1550nm		1.0	-	-	A/W
Rise/Fall				15		ns
Dynamic Impedance	0V					
	Class A		50	-	-	M ohm
	Class B		1.0	-	-	M ohm
	Class C		0.15	-	-	M ohm
Absolute Maximum Ratings						
Reverse Voltage						15 Volts
Forward Current						100 mA
Reverse Current						20 mA
Operating Temperature						-40°C to + 85°C
Storage Temperature						-40°C to + 85°C
Soldering Temperature						250°C